

Direct measurement of dopant distribution in an indivi

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Citation Report

#	ARTICLE	IF	CITATIONS
2	Crucial role of doping dynamics on transport properties of Sb-doped SnO ₂ nanowires. Applied Physics Letters, 2009, 95, 053105.	1.5	39
3	Correlating dopant distributions and electrical properties of boron-doped silicon nanowires. Applied Physics Letters, 2009, 95, .	1.5	44
4	Atom-Probe Tomography of Semiconductor Materials and Device Structures. MRS Bulletin, 2009, 34, 738-743.	1.7	42
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